

## PORTABLE EQUIPMENT APPLICATION

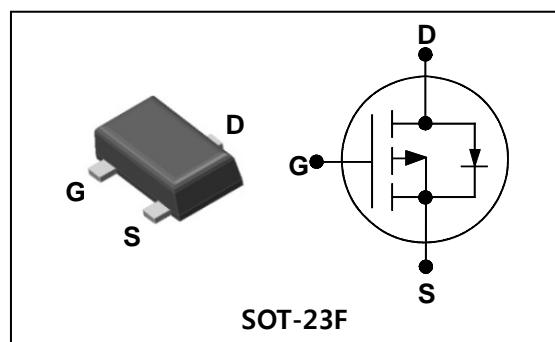
### Features

- Low Voltage :  $BV_{DSS} = -30V$ (Min.)
- Low  $V_{GS(th)}$  :  $V_{GS(th)} = -0.7 \sim -1.4V$
- Small footprint due to small package
- Low  $R_{DS(on)}$  :  $R_{DS(on)} = 91m\Omega$ (Max.)

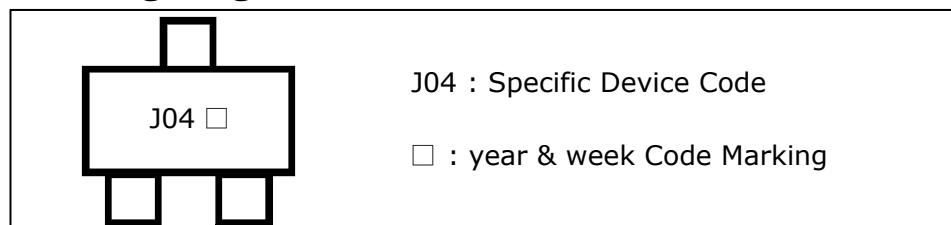
### Ordering Information

Type No.	Marking	Package Code
STJ004SF	J04 ①    ②	SOT-23F

### PIN Connection



### Marking Diagram



### Absolute maximum ratings ( $T_A=25^\circ C$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	-30	V
Gate-source voltage	$V_{GSS}$	$\pm 12$	V
Drain current (DC) *	$I_D$	-2.4	A
Drain current (Pulsed) *	$I_{DM}$	-9.6	A
Power dissipation **	$P_D$	0.35	W
Avalanche current (Single) ②	$I_{AS}$	-2.4	A
Single pulsed avalanche energy ②	$E_{AS}$	13	mJ
Avalanche current (Repetitive) ①	$I_{AR}$	-2.4	A
Repetitive avalanche energy ①	$E_{AR}$	1.1	mJ
Junction temperature	$T_J$	150	$^\circ C$
Storage temperature range	$T_{stg}$	-55~150	

\* Limited by maximum junction temperature

\*\* Device mounted on a glass-epoxy board

Characteristic	Symbol	Typ.	Max.	Unit
Thermal resistance	$R_{th(J-A)}$	-	357	$^\circ C/W$

**Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	$\text{BV}_{\text{DSS}}$	$I_D=-250\mu\text{A}, V_{GS}=0$	-30	-	-	V
Gate threshold voltage	$V_{GS(\text{th})}$	$I_D=-250\mu\text{A}, V_{DS}=V_{GS}$	-0.7	-	-1.4	V
Drain-source cut-off current	$I_{\text{DSS}}$	$V_{DS}=-20\text{V}, V_{GS}=0$	-	-	1	$\mu\text{A}$
Gate leakage current	$I_{\text{GSS}}$	$V_{DS}=0\text{V}, V_{GS}=\pm 12\text{V}$	-	-	$\pm 100$	nA
Drain-source on-resistance <sup>(4)</sup>	$R_{\text{DS(ON)}}$	$V_{GS}=-4.5\text{V}, I_D=-1.2\text{A}$	-	61	91	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}, I_D=-1.2\text{A}$	-	86	129	
Forward transfer conductance <sup>(4)</sup>	$g_{fs}$	$V_{DS}=-5\text{V}, I_D=-2.4\text{A}$	-	13.2	-	S
Input capacitance	$C_{iss}$	$V_{GS}=0\text{V}, V_{DS}=-10\text{V}, f=1\text{MHz}$	-	398	-	$\text{pF}$
Output capacitance	$C_{oss}$		-	82	-	
Reverse transfer capacitance	$C_{rss}$		-	46	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-10\text{V}, I_D=-2.4\text{A}$ $V_{GS}=-5\text{V}, R_G=25\Omega$	-	11	-	ns
Rise time	$t_r$		-	5.3	-	
Turn-off delay time	$t_{d(off)}$		-	7.6	-	
Fall time	$t_f$		-	5.3	-	
Total gate charge	$Q_g$	$V_{DD}=-10\text{V}, V_{GS}=-5\text{V}$ $I_D=-2.4\text{A}$	-	6.4	9.6	nC
Gate-source charge	$Q_{gs}$		-	2.8	4.2	
Gate-drain charge	$Q_{gd}$		(2)(4)	-	1.7	2.6

**Source-Drain Diode Ratings and Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

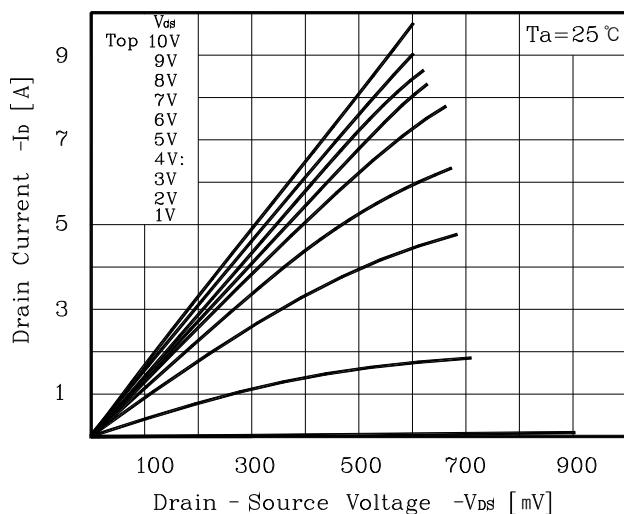
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Continuous source current	$I_s$	Integral reverse diode in the MOSFET	-	-	-0.5	A
Source current (Pulsed) <sup>(1)</sup>	$I_{SM}$		-	-	-2.0	
Forward voltage <sup>(4)</sup>	$V_{SD}$	$V_{GS}=0\text{V}, I_S=-0.5\text{A}$	-	-0.7	-1.2	V
Reverse recovery time	$t_{rr}$	$I_s=-2.4\text{A}, V_{GS}=0\text{V}$ $dI_F/dt=10\text{A}/\mu\text{s}$	-	29	-	ns
Reverse recovery charge	$Q_{rr}$		-	130	-	$\mu\text{C}$

Note :

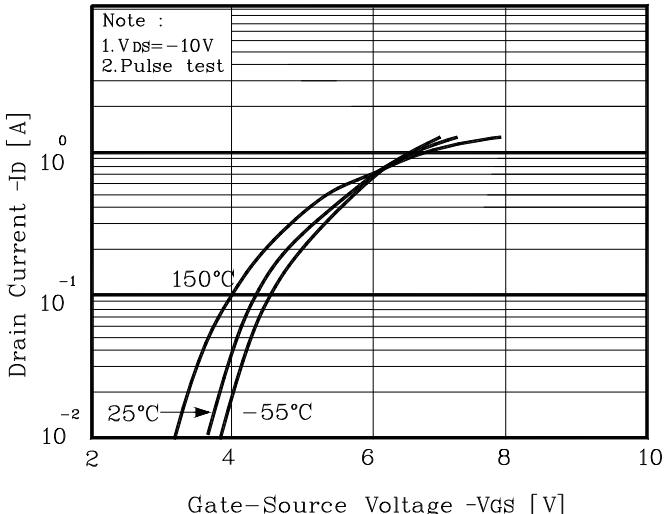
- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ②  $L=2.0\text{mH}, I_{AS}=-2.9\text{A}, V_{DD}=-15\text{V}, R_G=25\Omega$
- ③ Pulse Test : Pulse width  $\leq 300\text{us}$ , Duty cycle  $\leq 2\%$
- ④ Essentially independent of operating temperature

## P-CH Electrical Characteristic Curves

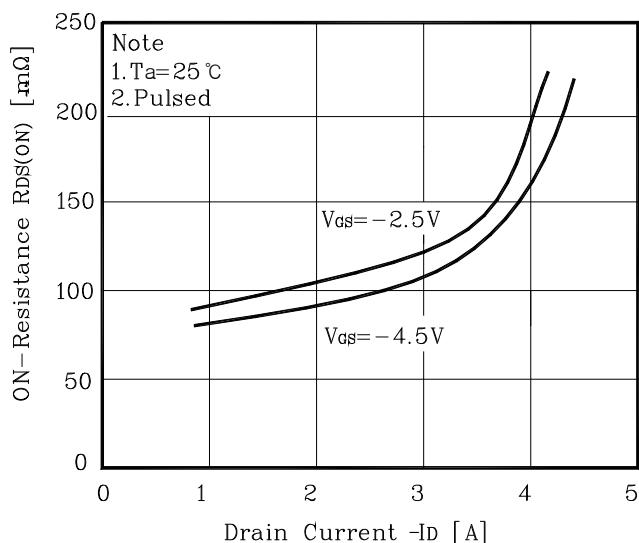
**Fig. 1  $I_D$  -  $V_{DS}$**



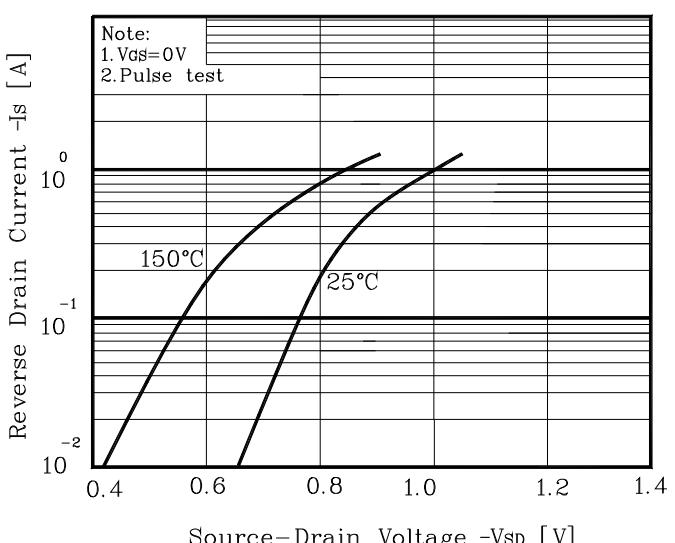
**Fig. 2  $I_D$  -  $V_{GS}$**



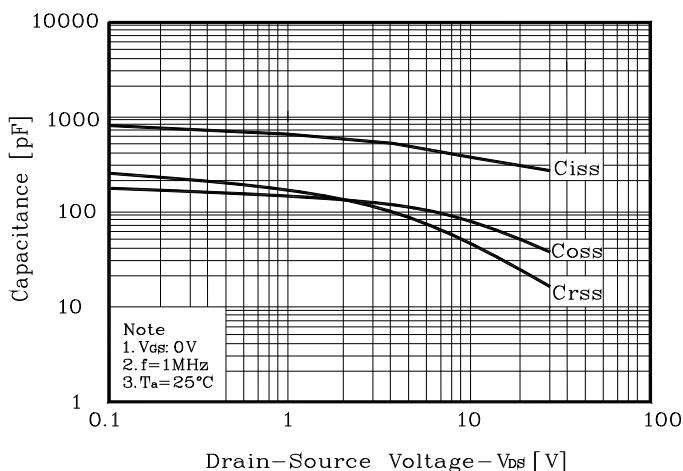
**Fig. 3  $R_{DS(on)}$  -  $I_D$**



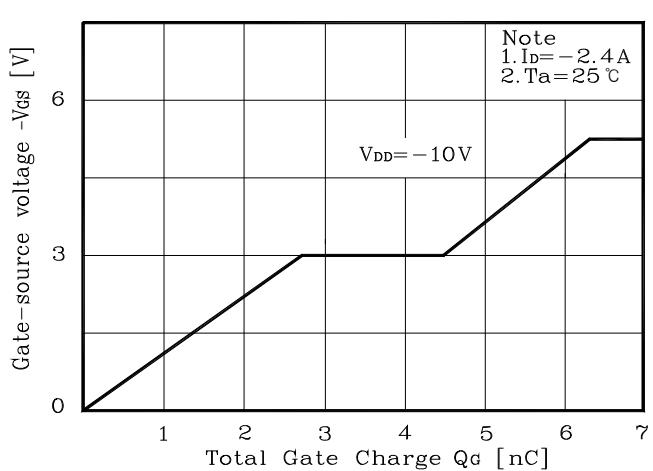
**Fig. 4  $I_S$  -  $V_{SD}$**



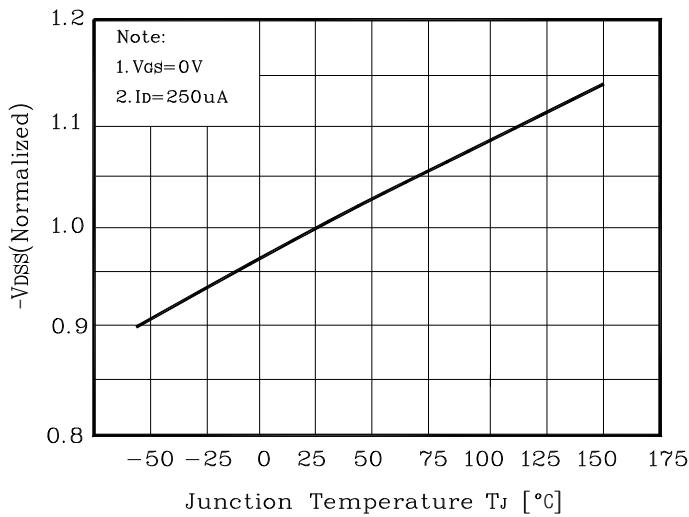
**Fig. 5 Capacitance -  $V_{DS}$**



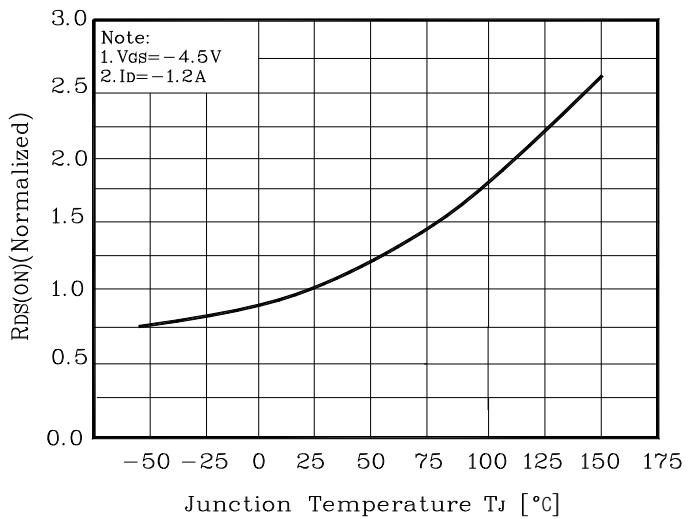
**Fig. 6  $V_{GS}$  -  $Q_G$**



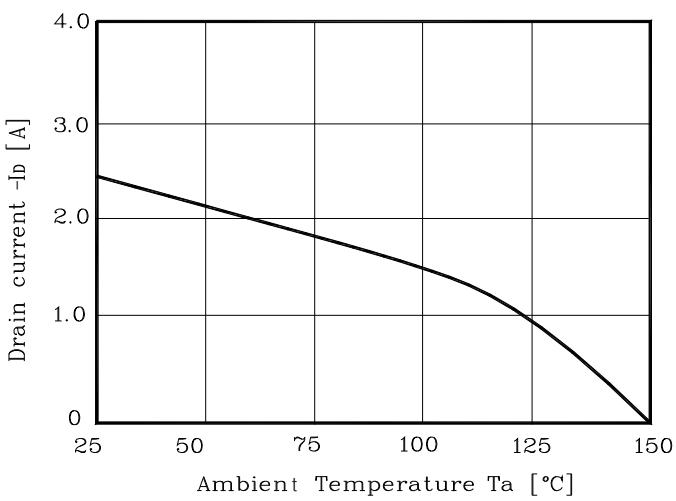
**Fig. 7  $V_{DSS}$  -  $T_J$**



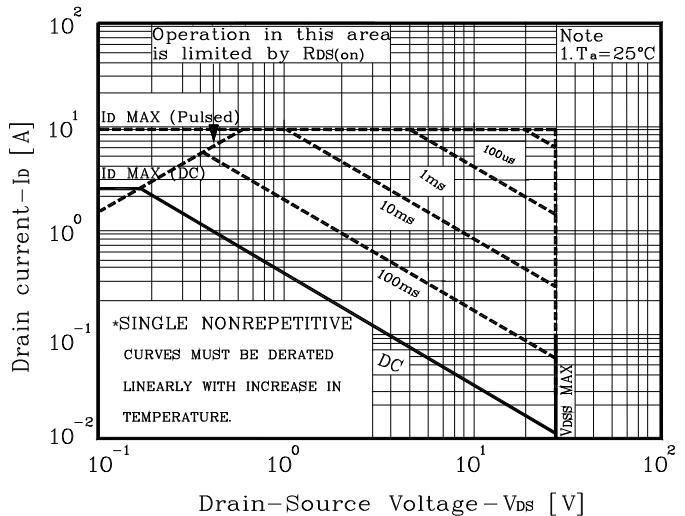
**Fig. 8  $R_{DS(on)}$  -  $T_J$**



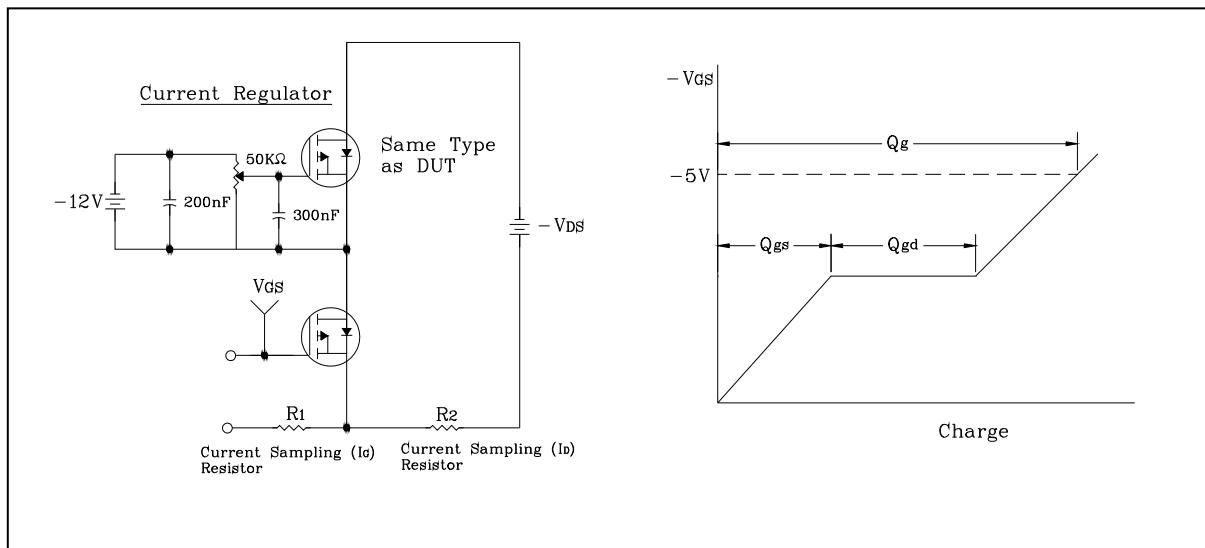
**Fig. 9  $I_D$  -  $T_a$**



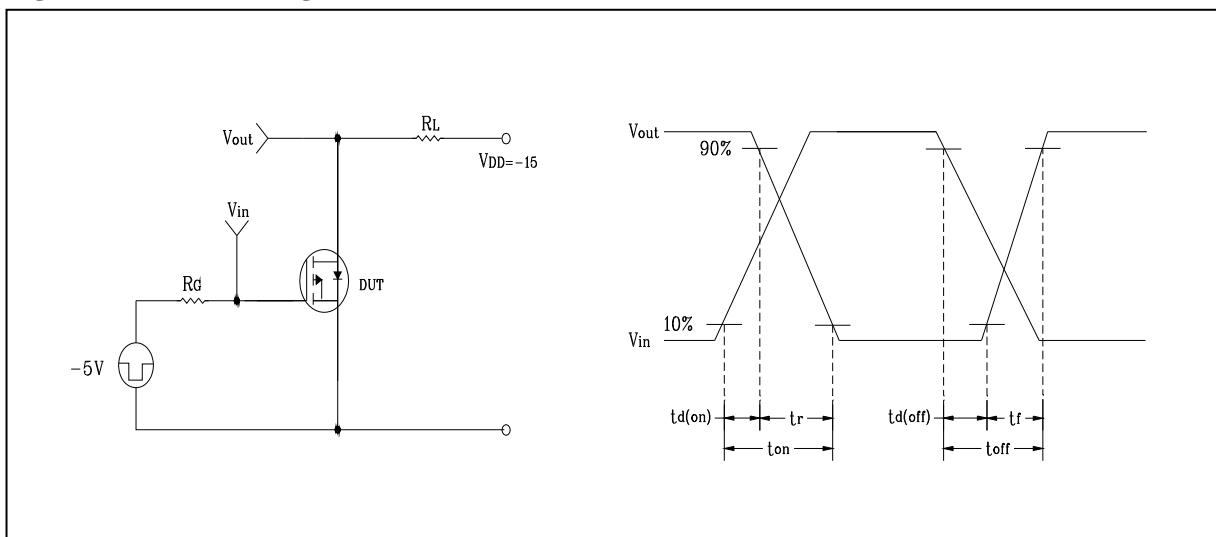
**Fig. 10 Safe Operating Area**



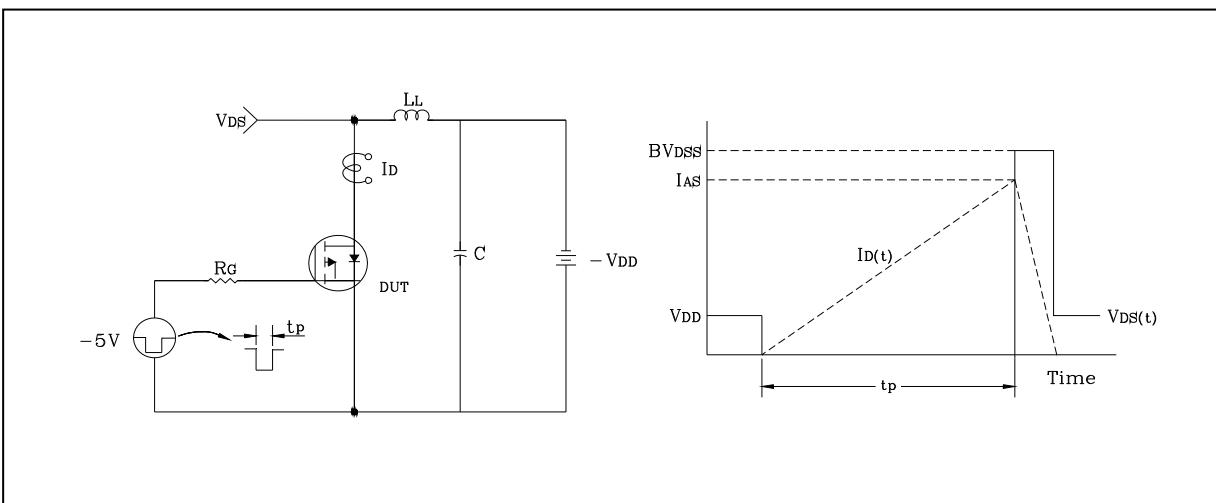
**Fig. 11 Gate Charge Test Circuit & Waveform**



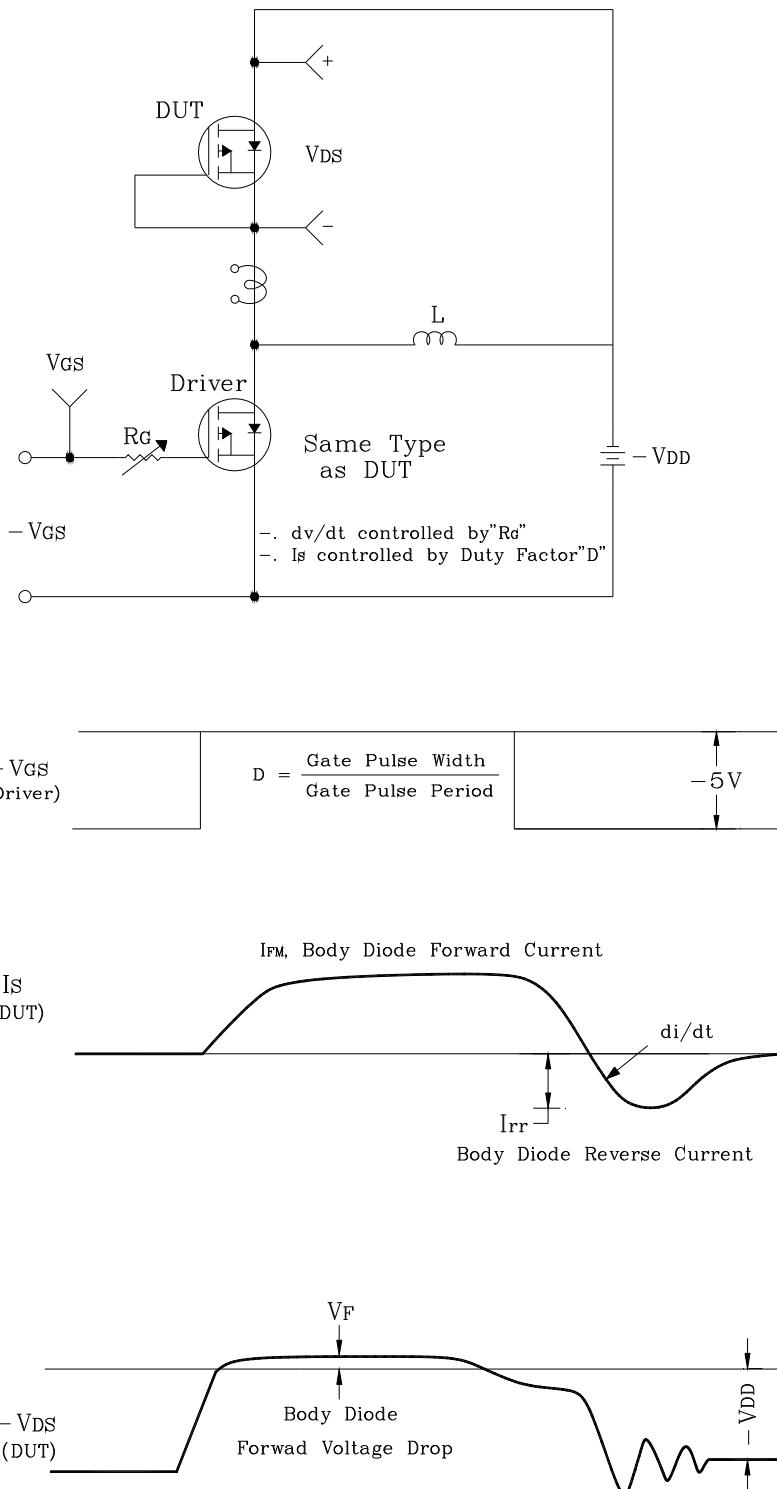
**Fig. 12 Resistive Switching Test Circuit & Waveform**



**Fig. 13 E<sub>AS</sub> Test Circuit & Waveform**

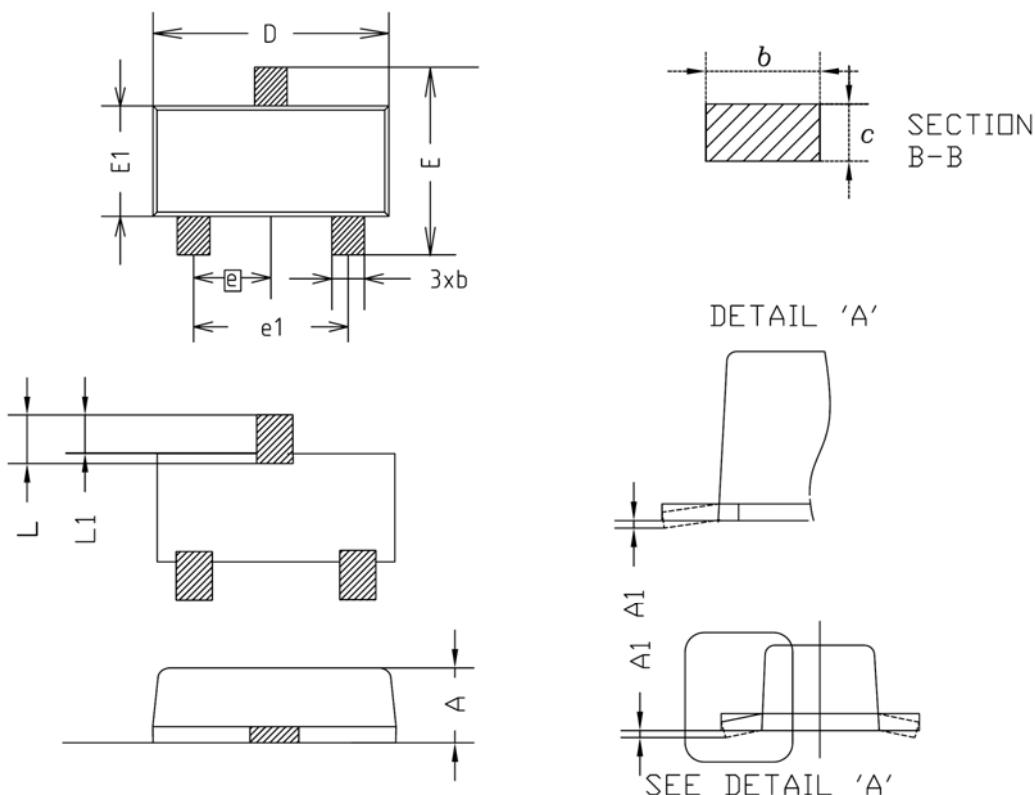


**Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform**

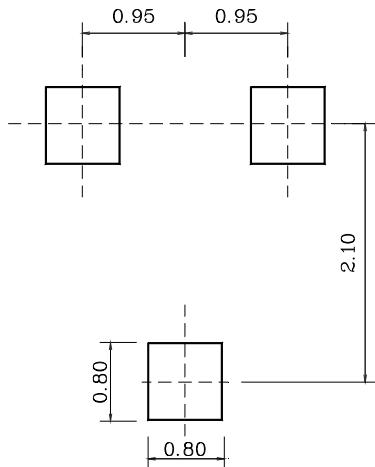


**Outline Dimension**

unit: mm



SYMBOL	MILLIMETER(mm)			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	0.80	0.90	1.00	
A1	0.00	-	0.10	
b	0.35	0.40	0.45	
c	0.10	0.15	0.20	
D	2.80	2.90	3.00	
E	2.30	2.40	2.50	
E1	1.50	1.60	1.70	
e	0.95BSC			
e1	1.80	1.90	2.00	
L	0.48	0.58	0.68	
L1	0.30	-	0.50	

**\* Recommended Land Pattern [unit: mm]**

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